

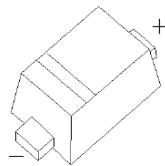


BAS516WT

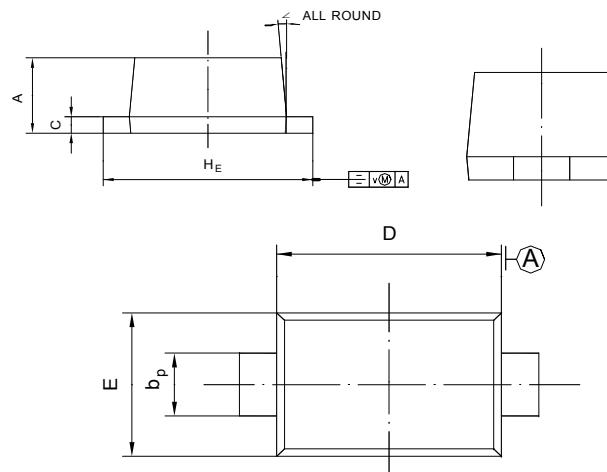
FAST SWITCHING DIODE

FEATURES

- Small Package
- Low Reverse Current
- Fast Switching Speed
- Surface Mount Package Ideally Suited for Automatic Insertion



SOD-523



UNIT	A	b _p	C	D	E	H _E	V	Ζ
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{RM}	Non-Repetitive Peak Reverse Voltage	100	V
V _{RRM}	Peak Repetitive Reverse Voltage	75	V
V _{RWM}	Working Peak Reverse Voltage		
V _{R(RMS)}	RMS Reverse Voltage	53	V
I _o	Average Rectified Output Current	250	mA
I _{FSM}	Non-repetitive Peak Forward Surge Current @ t=8.3ms	2.0	A
P _D	Power Dissipation	150	mW
R _{θJA}	Thermal Resistance from Junction to Ambient	833	°C/W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C

BAS516WT

ELECTRICAL CHARACTERISTICS($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(\text{BR})}$	$I_R=100\mu\text{A}$	75			V
Reverse current	I_R	$V_R=25\text{V}$			30	nA
		$V_R=75\text{V}$			1	μA
Forward voltage	V_F	$I_F=1\text{mA}$			0.715	V
		$I_F=10\text{mA}$			0.855	V
		$I_F=50\text{mA}$			1	V
		$I_F=150\text{mA}$			1.25	V
Total capacitance	C_{tot}	$V_R=0\text{V}, f=1\text{MHz}$			1	pF
Reverse recovery time	t_{rr}	$I_F= I_R =10\text{mA}, I_{rr}=0.1*I_R, R_L=100\Omega$			4	ns

RATING AND CHARACTERISTIC CURVES (BAS516WT)

